

**Erratum: Degradation of Boron-Doped Czochralski-Grown Silicon Solar Cells  
[Phys. Rev. Lett., 93, 055504 (2004)]**

J. Adey, R. Jones, D.W. Palmer, P.R. Briddon, and S. Öberg  
(Received 31 August 2004; published 14 October 2004)

DOI: 10.1103/PhysRevLett.93.169904

PACS numbers: 61.72.Bb, 61.72.Ji, 71.15.Nc, 71.55.-i, 99.10.Cd

The description of the diffusion mechanism of  $O_{2i}$  in the caption of Fig. (3) contained an error in the original article. It should have read: “A configuration-coordinate diagram for the oxygen dimer. Arrows show the proposed thermally assisted Bourgoin diffusion mechanism with a thermal barrier of 0.3 eV.  $O_{2i}^{++sq}$  at *A* first captures a photogenerated or injected electron and, after overcoming a 0.2 eV barrier, changes its configuration to  $O_{2i}^{+st}$ . It then traps a hole becoming  $O_{2i}^{++st}$ , and executes a diffusion jump to  $O_{2i}^{++sq}$  at *B* after overcoming a thermal barrier of 0.3 eV.”

This mechanism was described correctly in the main text.